Erratum: Thermalization of photoexcited carriers in two-dimensional transition metal dichalcogenides and internal quantum efficiency of van der Waals heterostructures
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Dinesh Yadav , Maxim Trushin, and Fabian Pauly

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We have found the following mistake in our published paper. The parameters λ_e and λ_h should be dimensionless, and the corrected Eq. (6) reads (see also Ref. [1], containing the correct definitions)

$$\begin{aligned} f_{n\mathbf{k}}(0, T) &= f_{n\mathbf{k}}^{(0)}(T) - \lambda_h e^{-\frac{(\varepsilon_{n\mathbf{k}} + \xi + \Delta/2)^2}{2\sigma^2}}, & \varepsilon_{n\mathbf{k}} < \varepsilon_F, \\ f_{n\mathbf{k}}(0, T) &= f_{n\mathbf{k}}^{(0)}(T) + \lambda_e e^{-\frac{(\varepsilon_{n\mathbf{k}} - \xi - \Delta/2)^2}{2\sigma^2}}, & \varepsilon_{n\mathbf{k}} \geq \varepsilon_F. \end{aligned} \quad (1)$$

Due to this modification the photoexcited carrier density used in our calculations changes from $7 \times 10^{12} \text{ cm}^{-2}$ to $3.3 \times 10^{14} \text{ cm}^{-2}$ throughout the paper, i.e., it becomes by a factor of $eV/\sqrt{2\pi\sigma^2} \approx 47$ larger than originally stated. Since this carrier density remains sufficiently low, the relaxation time approximation (RTA) still applies, and neither figures nor outcomes are affected by this change.

[1] D. Yadav, F. Pauly, and M. Trushin, Charge-carrier thermalization in bulk and monolayer CdTe from first principles, *Phys. Rev. B* **103**, 125113 (2021).

Correction: Equation (1) contained two sign errors and has been fixed.